



Silicon Wafer NA TC Chapter

Summer Standards Meetings

Tuesday, July 13, 2021

2:00 pm - 6:00 pm Pacific

Online

AGENDA

1.0 Welcome / Call to Order

1.1 Introductions

1.2 Meeting Reminders (*Membership Requirement, Antitrust and Intellectual Property Reminders, Effective Meeting Guidelines*)

1.3 Agenda Review

2.0 Review of Schedule for the next meeting (?)

3.0 Review and Approval of Previous Meeting Minutes (SEMICON West, July 9, 2019)

4.0 Liaison Report

4.1 European Committee

4.2 Japan Committee

4.3 GCS

5.0 Staff Report

6.0 Regulations Change Report (if applicable)

7.0 Ballot Review

7.1 Cycle 4-2021

- 7.1.1 6753 Reapproval of SEMI MF723-0307E (Reapproved 0412)E Practice for Conversion Between Resistivity and Dopant or Carrier Density for Boron-Doped, Phosphorous-Doped, and Arsenic-Doped Silicon
- 7.1.2 6754 Reapproval of SEMI MF674-0316 Practice for Preparing Silicon for Spreading Resistance Measurements
- 7.1.3 6755 Reapproval of SEMI MF533-0310 (Reapproved 0416) Test Method for Thickness and Thickness Variation of Silicon Wafers
- 7.1.4 6756 Reapproval of SEMI MF43-0316 Test Method for Resistivity of Semiconductor Materials
- 7.1.5 6757 Reapproval of SEMI MF42-0316 Test Method for Conductivity Type of Extrinsic Semiconducting Materials
- 7.1.6 6758 Reapproval of SEMI MF2139-1103 (Reapproved 0416) Test Method for Measuring Nitrogen Concentration in Silicon Substrates by Secondary Ion Mass Spectrometry
- 7.1.7 6759 Reapproval of SEMI MF1811-1116 Guide for Estimating the Power Spectral Density Function and Related Finish Parameters from Surface Profile Data



- 7.1.8 6760 Reapproval of SEMI MF1771-0416 Test Method for Evaluating Gate Oxide Integrity by Voltage Ramp Technique
- 7.1.9 6761 Reapproval of SEMI MF1535-1015 Test Method for Carrier Recombination Lifetime in Electronic-Grade Silicon Wafers by Noncontact Measurement of Photoconductivity Decay by Microwave Reflectance
- 7.1.10 6762 Reapproval of SEMI MF1529-1110 (Reapproved 1115) Test Method for Sheet Resistance Uniformity Evaluation by In-Line Four-Point Probe with the Dual-Configuration Procedure
- 7.1.11 6763 Reapproval of SEMI MF1239-0305 (Reapproved 0416) Test Method for Oxygen Precipitation Characteristics of Silicon Wafers by Measurement of Interstitial Oxygen Reduction
- 7.1.12 6764 Reapproval of SEMI MF1153-1110 (Reapproved 1015) Test Method for Characterization of Metal-Oxide Silicon (MOS) Structures by Capacitance-Voltage Measurements
- 7.1.13 6765 Reapproval of SEMI MF1152-0316 Test Method for Dimensions of Notches on Silicon Wafers
- 7.1.14 6766 Reapproval of SEMI M57-0316 Specification for Silicon Annealed Wafers

7.2 Cycle 5-2021

- 7.2.1 6787 Reapproval of SEMI MF951 - Test Method for Determination of Radial Interstitial Oxygen Variation in Silicon Wafers
- 7.2.2 6788 Reapproval of SEMI MF847 - Test Method for Measuring Crystallographic Orientation of Flats on Single Crystal Silicon Wafers by X-Ray Techniques
- 7.2.3 6789 Reapproval of SEMI MF81 - Test Method for Measuring Radial Resistivity Variation on Silicon Wafers
- 7.2.4 6790 Reapproval of SEMI MF1809 - Guide for Selection and Use of Etching Solutions to Delineate Structural Defects in Silicon
- 7.2.5 6791 Reapproval of SEMI MF1810 - Test Method for Counting Preferentially Etched or Decorated Surface Defects in Silicon Wafers
- 7.2.6 6792 Reapproval of SEMI MF1725 - Practice for Analysis of Crystallographic Perfection of Silicon Ingots
- 7.2.7 6793 Reapproval of SEMI MF1726 - Practice for Analysis of Crystallographic Perfection of Silicon Wafers
- 7.2.8 6794 Reapproval of SEMI MF1727 - Practice for Detection of Oxidation Induced Defects in Polished Silicon Wafers
- 7.2.9 6795 Reapproval of SEMI MF1617 - Test Method for Measuring Surface Sodium, Aluminum, Potassium, and Iron on Silicon and EPI Substrates by Secondary Ion Mass Spectrometry
- 7.2.10 6796 Reapproval of SEMI MF1618 - Practice for Determination of Uniformity of Thin Films on Silicon Wafers
- 7.2.11 6797 Reapproval of SEMI MF154 - Guide for Identification of Structures and Contaminants Seen on Specular Silicon Surfaces
- 7.2.12 6798 Reapproval of SEMI MF1389 - Test Method for Photoluminescence Analysis of Single Crystal Silicon for III-V Impurities



- 7.2.13 6799 Reapproval of SEMI M66 - Test Method to Extract Effective Work Function in Oxide and High-K Gate Stacks Using the MIS Flat Band Voltage-Insulator Thickness Technique
- 7.2.14 6800 Reapproval of SEMI M16 - Specification for Polycrystalline Silicon
- 7.2.15 6801 Reapproval of SEMI M17 - Guide for a Universal Wafer Grid

7.3 Cycle 4-2020

- 7.3.1 6462 Line Item Revision to SEMI M1-0918, SPECIFICATION FOR POLISHED SINGLE CRYSTAL SILICON WAFERS

8.0 Task Force Reports

- 8.1 Int'l Advanced Wafer Geometry Task Force /Noel Poduje (SMS)
- 8.2 Int'l Automated Advanced Surface Inspection Task Force/ Kurt Haller (KLA)
- 8.3 Int'l SOI Wafers TF/Gerd Pfeiffer (SOITEC)
- 8.4 Int'l Test Methods TF/Dinesh Gupta (STA)
- 8.5 Int'l Polished Wafers (Substrates) TF/TBD

9.0 Old Business

10.0 New Business

- 10.1 5 Year Review

11.0 Action Item Review

- 11.1 Open Action Items
- 11.2 New Action Items

12.0 Next Meeting and Adjournment

- 12.1 The next meeting of the NA Silicon Wafer committee ?